



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

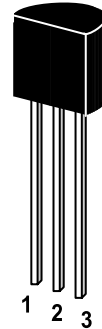
ST 2SC2001

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

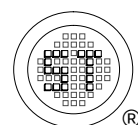


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	25	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_c	700	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$



Dated : 07/12/2002



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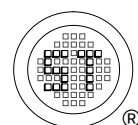
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=1V$, $I_C=100mA$					
Current Gain Group O	h_{FE}	90	-	180	-
Y	h_{FE}	135	-	270	-
G	h_{FE}	200	-	400	-
at $V_{CE}=1V$, $I_C=700mA$	h_{FE}	50	-	-	-
Collector Base Breakdown Voltage at $I_C=10\mu A$	$V_{(BR)CBO}$	30	-	-	V
Base Emitter Voltage at $I_C=10mA$, $V_{CE}=6V$	V_{BE}	0.6	-	0.7	V
Emitter Cutoff Current at $V_{EB}=5V$	I_{EBO}	-	-	0.1	μA
Collector Cutoff Current at $V_{CB}=30V$	I_{CBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=700mA$, $I_B=70mA$	$V_{CE(sat)}$	-	0.2	0.6	V
Base Saturation Voltage at $I_C=700mA$, $I_B=70mA$	$V_{BE(sat)}$	-	0.95	1.2	V
Gain Bandwidth Product at $V_{CE}=6V$, $I_C=10mA$	f_T	50	170	-	MHz
Output Capacitance at $V_{CB}=6V$, $f=1MHz$	C_{OB}	-	13	25	pF



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